AiP74LV32
Quad 2-input Or Gate

Product Specification

Specification Revision History:

Version	Date	Description
2017-05-A1	2017-05	New
2021-12-A2	2021-12	Modify Ordering Information
2022-02-A3	2022-02	Modify ambient temperature to -40℃~+105℃ and add electrical characteristics of -40℃~+105℃

1、General Description

The AiP74LV32 is a low-voltage Si-gate CMOS device that is pin and function compatible with AiP74HC32 and AiP74HCT32.

The AiP74LV32 provides a quad 2-input OR function.

Features:

- Wide operating voltage: 1.0V to 5.5V
- Optimized for low voltage applications: 1.0V to 3.6V
- Accepts TTL input levels between V_{CC}=2.7V and V_{CC}=3.6V
- Typical output ground bounce < 0.8V at V_{CC}=3.3V and T_{amb}=25℃
- Typical HIGH-level output voltage (V_{OH}) undershoot: >2V at V_{CC}=3.3V and T_{amb}=25℃
- Specified from -40℃ to +105℃
- Packaging information: DIP14/SOP14/TSSOP14

Ordering Information:

Tube packing specifications:

Part number	Packaging form	Marking code	Tube quantity	Boxed tube quantity	Boxed quantity	Notes
AiP74LV32DA14.TB	DIP14	74LV32	25 PCS/tube	40 tube/box	1000 PCS/box	Dimensions of plastic enclosure: 19.0mm×6.4mm Pin spacing: 2.54mm
AiP74LV32SA14.TB	SOP14	74LV32	50 PCS/tube	200 tube/box	10000 PCS/box	Dimensions of plastic enclosure: 8.7mm×3.9mm Pin spacing: 1.27mm
AiP74LV32TA14.TB	TSSOP14	74LV32	94 PCS/tube	200 tube/box	18800 PCS/box	Dimensions of plastic enclosure: 5.0mm×4.4mm Pin spacing: 0.65mm

Reel packing specifications:

Part number	Packaging form	Marking code	Reel quantity	Boxed reel quantity	Notes
AiP74LV32SA14.TR	SOP14	74LV32	4000 PCS/reel	8000 PCS/box	Dimensions of plastic enclosure: 8.7mm×3.9mm Pin spacing: 1.27mm
AiP74LV32TA14.TR	TSSOP14	74LV32	5000 PCS/reel	10000 PCS/box	Dimensions of plastic enclosure: 5.0mm×4.4mm Pin spacing: 0.65mm

Note: If the physical information is inconsistent with the ordering information, please refer to the actual product.

2、Block Diagram And Pin Description

2.1、Block Diagram

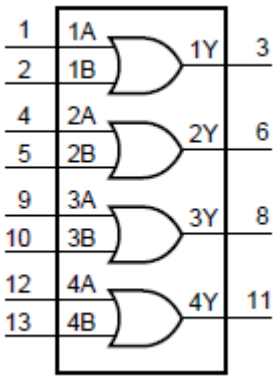


Figure 1. Logic symbol

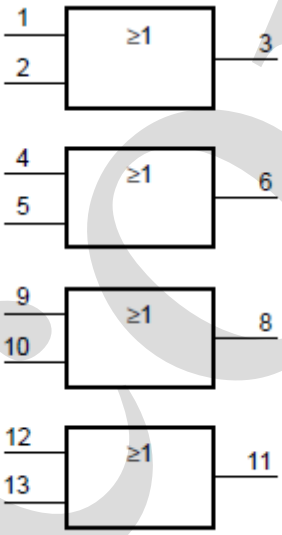


Figure 2. IEC logic symbol

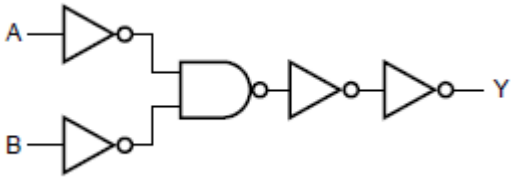
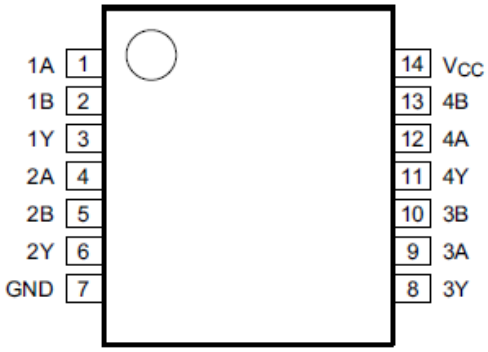


Figure 3. Logic diagram (one gate)

2.2、Pin Configurations



2.3、Pin Description

Pin No.	Pin Name	Description
1	1A	data input
2	1B	data input
3	1Y	data output
4	2A	data input
5	2B	data input
6	2Y	data output
7	GND	ground (0V)
8	3Y	data output
9	3A	data input
10	3B	data input
11	4Y	data output
12	4A	data input
13	4B	data input
14	V_{CC}	supply voltage

2.4、Function Table

Input		Output
nA	**nB**	**nY**
H	X	H
X	H	H
L	L	L

Note: H=HIGH voltage level; L=LOW voltage level; X=don't care.

3、Electrical Parameter

3.1、Absolute Maximum Ratings

(Voltages are referenced to GND(ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions		Min.	Max.	Unit
supply voltage	V_{CC}	-		-0.5	+7.0	V
input clamping current	I_{IK}	V_I < -0.5V or V_I > V_{CC}+0.5V		-	±20	mA
output clamping current	I_{OK}	V_O < -0.5V or V_O > V_{CC}+0.5V		-	±50	mA
output current	I_O	V_O= -0.5V to (V_{CC}+0.5V)		-	±25	mA
supply current	I_{CC}	-		-	50	mA
ground current	I_{GND}	-		-50	-	mA
storage temperature	T_{stg}	-		-65	+150	℃
total power dissipation	P_{tot}	-		-	500	mW
Soldering temperature	T_L	10s	DIP	245		℃
			SOP	250		

Note:

[1] For DIP14 packages: above 70℃ the value of P_{tot} derates linearly with 12mW/K.

[2] For SOP14 packages: above 70℃ the value of P_{tot} derates linearly with 8mW/K.

[3] For (T)SSOP14 packages: above 60℃ the value of P_{tot} derates linearly with 5.5mW/K.

3.2、Recommended Operating Conditions

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
supply voltage	V_{CC}	-	1.0	3.3	5.5	V
input voltage	V_I	-	0	-	V_{CC}	V
output voltage	V_O	-	0	-	V_{CC}	V
ambient temperature	T_{amb}	-	-40	-	+105	℃
input transition rise and fall rate	$\Delta t/\Delta V$	V_{CC}=1.0V to 2.0V	-	-	500	ns/V
		V_{CC}=2.0V to 2.7V	-	-	200	ns/V
		V_{CC}=2.7V to 3.6V	-	-	100	ns/V
		V_{CC}=3.6V to 5.5V	-	-	50	ns/V

Note: The static characteristics are guaranteed from V_{CC}=1.2V to V_{CC}=5.5V, but LV devices are guaranteed to function down to V_{CC}=1.0V (with input levels GND or V_{CC}).

3.3、Electrical Characteristics

3.3.1、DC Characteristics 1

(T_{amb}=-40℃ to +85℃, voltages are referenced to GND (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Unit
HIGH-level input voltage	V_{IH}	V_{CC}=1.2V		V_{CC}	0.6	-	V
		V_{CC}=2.0V		1.4	-	-	V
		V_{CC}=2.7V to 3.6V		2.0	-	-	V
		V_{CC}=4.5V to 5.5V		0.7×V_{CC}	-	-	V
LOW-level input voltage	V_{IL}	V_{CC}=1.2V		-	0.4	GND	V
		V_{CC}=2.0V		-	-	0.6	V
		V_{CC}=2.7V to 3.6V		-	-	0.8	V
		V_{CC}=4.5V to 5.5V		-	-	0.3×V_{CC}	V
HIGH-level output voltage	V_{OH}	V_I = V_{IH} or V_{IL}	I_O=-100uA; V_{CC}=1.2V	-	1.2	-	V
			I_O=-100uA; V_{CC}=2.0V	1.8	2.0	-	V
			I_O=-100uA; V_{CC}=2.7V	2.5	2.7	-	V
			I_O=-100uA; V_{CC}=3.0V	2.8	3.0	-	V
			I_O=-100uA; V_{CC}=4.5V	4.3	4.5	-	V
			I_O=-6mA; V_{CC}=3.0V	2.4	2.82		V
			I_O=-12mA; V_{CC}=4.5V	3.6	4.2	-	V
LOW-level output voltage	V_{OL}	V_I = V_{IH} or V_{IL}	I_O=100uA; V_{CC}=1.2V	-	0	-	V
			I_O=100uA; V_{CC}=2.0V	-	0	0.2	V
			I_O=100uA; V_{CC}=2.7V	-	0	0.2	V
			I_O=100uA; V_{CC}=3.0V	-	0	0.2	V
			I_O=100uA; V_{CC}=4.5V	-	0	0.2	V
			I_O=6mA; V_{CC}=3.0V	-	0.25	0.40	V
			I_O=12mA; V_{CC}=4.5V	-	0.35	0.55	V
input leakage current	I_I	V_I=V_{CC} or GND; V_{CC}=5.5V		-	-	1.0	uA
supply current	I_{CC}	V_I=V_{CC} or GND; I_O=0A; V_{CC}=5.5V		-	-	20	uA
additional supply current	ΔI_{CC}	per input; V_I=V_{CC}-0.6V; V_{CC}=2.7V to 3.6V		-	-	500	uA
input capacitance	C_I	-		-	3.5	-	pF

Note: All typical values are measured at T_{amb}=25℃

3.3.2、DC Characteristics 2

(T_{amb}=-40℃ to +105℃, voltages are referenced to GND (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Unit
HIGH-level input voltage	V_{IH}	V_{CC}=1.2V		V_{CC}	0.6	-	V
		V_{CC}=2.0V		1.4	-	-	V
		V_{CC}=2.7V to 3.6V		2.0	-	-	V
		V_{CC}=4.5V to 5.5V		0.7× V_{CC}	-	-	V
LOW-level input voltage	V_{IL}	V_{CC}=1.2V		-	0.4	GND	V
		V_{CC}=2.0V		-	-	0.6	V
		V_{CC}=2.7V to 3.6V		-	-	0.8	V
		V_{CC}=4.5V to 5.5V		-	-	0.3× V_{CC}	V
HIGH-level output voltage	V_{OH}	V_I = V_{IH} or V_{IL}	I_O=-100uA; V_{CC}=2.0V	1.8	-	-	V
			I_O=-100uA; V_{CC}=2.7V	2.5	-	-	V
			I_O=-100uA; V_{CC}=3.0V	2.8	-	-	V
			I_O=-100uA; V_{CC}=4.5V	4.3	-	-	V
			I_O=-6mA; V_{CC}=3.0V	2.2	-	-	V
			I_O=-12mA; V_{CC}=4.5V	3.5	-	-	V
LOW-level output voltage	V_{OL}	V_I = V_{IH} or V_{IL}	I_O=100uA; V_{CC}=2.0V	-	-	0.2	V
			I_O=100uA; V_{CC}=2.7V	-	-	0.2	V
			I_O=100uA; V_{CC}=3.0V	-	-	0.2	V
			I_O=100uA; V_{CC}=4.5V	-	-	0.2	V
			I_O=6mA; V_{CC}=3.0V	-	-	0.50	V
			I_O=12mA; V_{CC}=4.5V	-	-	0.65	V
input leakage current	I_I	V_I=V_{CC} or GND; V_{CC}=5.5V		-	-	1.0	uA
supply current	I_{CC}	V_I=V_{CC} or GND; I_O=0A; V_{CC}=5.5V		-	-	40	uA
additional supply current	ΔI_{CC}	per input; V_I=V_{CC}-0.6V; V_{CC}=2.7V to 3.6V		-	-	850	uA

Note: All typical values are measured at T_{amb}=25℃

3.3.3、AC Characteristics 1

(T_{amb}=-40℃ to +85℃, voltages are referenced to GND (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Unit
nA, nB to nY; propagation delay	t_{pd}	see Figure 5	V_{CC}=1.2V	-	40	-	ns
			V_{CC}=2.0V	-	14	22	ns
			V_{CC}=2.7V	-	10	16	ns
			V_{CC}=3.0V to 3.6V; C_L=15pF	-	6.0	-	ns
			V_{CC}=3.0V to 3.6V	-	8.0	13	ns
			V_{CC}=4.5V to 5.5V	-	-	10	ns
Power dissipation capacitance	C_{PD}	C_L=50pF; f_i=1MHz; V_I=GND to V_{CC}		-	16	-	pF

Note:

[1] Typical values are measured at T_{amb}=25℃.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] Typical values are measured at nominal supply voltage (V_{CC}=3.3V).

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in uW).

$P_D=C_{PD}\times V_{CC}^2\times f_i\times N+\sum(C_L\times V_{CC}^2\times f_o)$ where:

f_i=input frequency in MHz;

f_o=output frequency in MHz;

C_L=output load capacitance in pF;

V_{CC}=supply voltage in V;

N=number of inputs switching;

$\sum(C_L\times V_{CC}^2\times f_o)$=sum of outputs.

3.3.4、AC Characteristics 2

(T_{amb}=-40℃ to +105℃, voltages are referenced to GND (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Unit
nA, nB to nY; propagation delay	t_{pd}	see Figure 5	V_{CC}=2.0V	-	-	28	ns
			V_{CC}=2.7V	-	-	20	ns
			V_{CC}=3.0V to 3.6V	-	-	16	ns
			V_{CC}=4.5V to 5.5V	-	-	13	ns

Note:

[1] Typical values are measured at T_{amb}=25℃.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] Typical values are measured at nominal supply voltage (V_{CC}=3.3V).

4、Testing Circuit

4.1、AC Testing Circuit

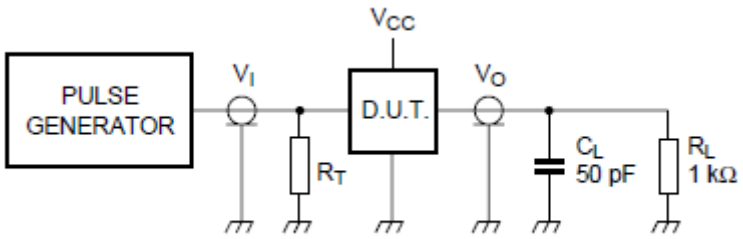


Figure 4. Test circuit for switching times

Definitions for test circuit:

R_L=Load resistance.

C_L=Load capacitance including jig and probe capacitance.

R_T=Termination resistance should be equal to the output impedance Z_o of the pulse generator.

4.2、AC Testing Waveforms

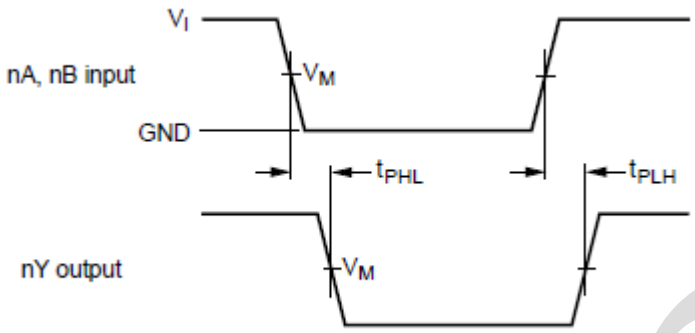


Figure 5. The input (nA, nB) to output (nY) propagation delays

4.3、Measurement Points

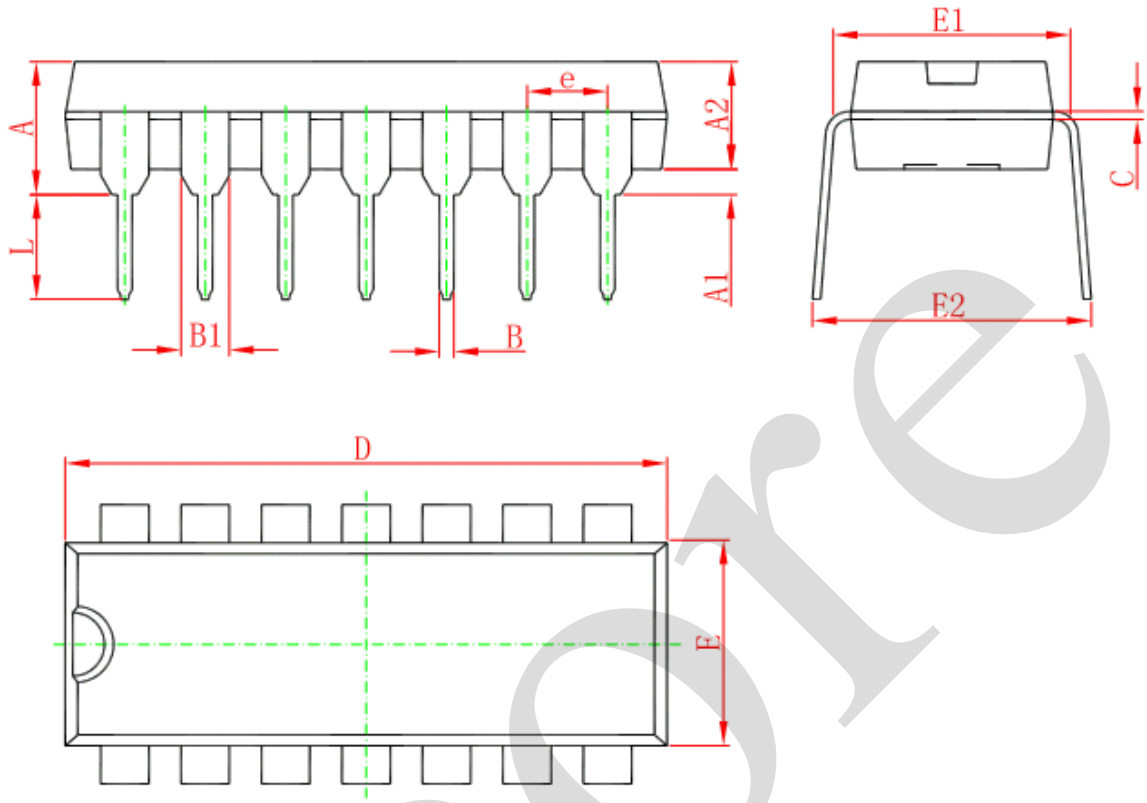
Supply voltage	Input	Output
V_{CC}	V_M	V_M
<2.7V	$0.5\times V_{CC}$	$0.5\times V_{CC}$
2.7V to 3.6V	1.5V	1.5V
≥4.5V	$0.5\times V_{CC}$	$0.5\times V_{CC}$

4.4、Test Data

Supply voltage	Input	
V_{CC}	V_I	t_r , t_f
<2.7V	V_{CC}	≤ 2.5ns
2.7V to 3.6V	2.7V	≤ 2.5ns
≥4.5V	V_{CC}	≤ 2.5ns

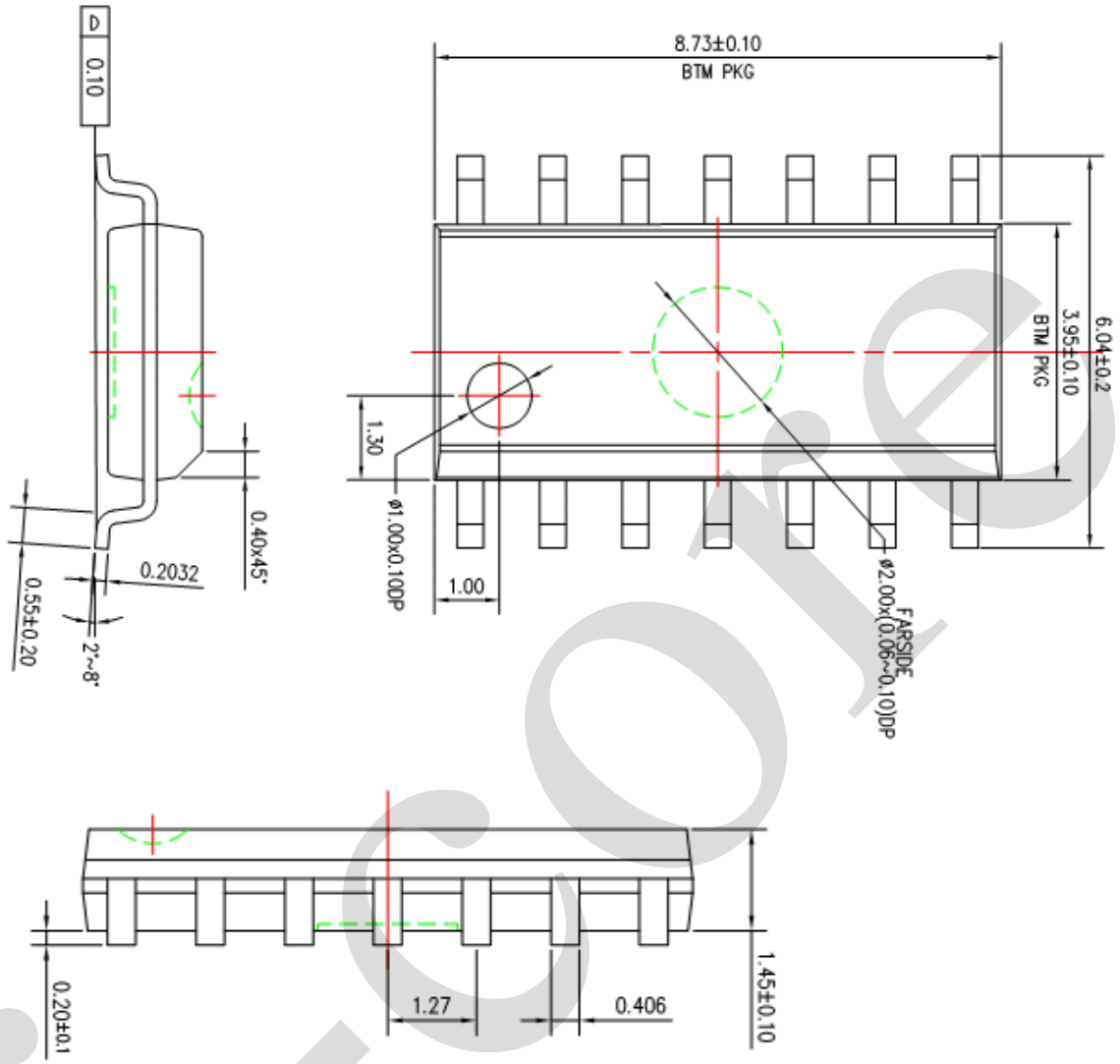
5、Package Information

5.1、DIP14

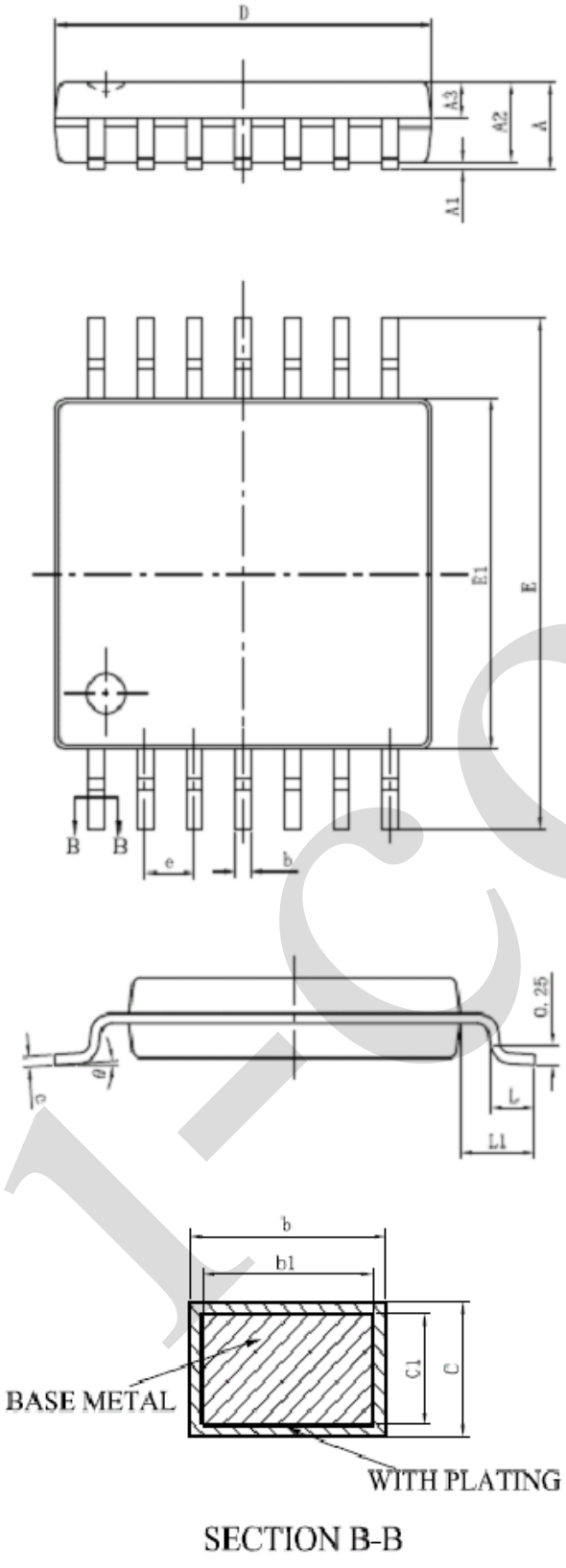


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.710	4.310	0.146	0.170
A1	0.510		0.020	
A2	3.200	3.600	0.126	0.142
B	0.380	0.570	0.015	0.022
B1	1.524 (BSC)		0.060 (BSC)	
C	0.204	0.360	0.008	0.014
D	18.800	19.200	0.740	0.756
E	6.200	6.600	0.244	0.260
E1	7.320	7.920	0.288	0.312
e	2.540 (BSC)		0.100 (BSC)	
L	3.000	3.600	0.118	0.142
E2	8.400	9.000	0.331	0.354

5.2、SOP14


0.10
8.73±0.10
BTM PKG
6.04±0.2
3.95±0.10
BTM PKG
1.30
Ø1.00x0.100P
1.00
Ø2.00x(0.06~0.10)DP
FARSIDE
0.40x45°
0.2032
0.55±0.20
2°~8°
0.20±0.1
1.27
0.406
1.45±0.10

5.3、TSSOP14



SECTION B-B

SYMBOL	MILLIMETER	
	MIN	MAX
A	—	1.20
A1	0.05	0.15
A2	0.90	1.05
A3	0.39	0.49
b	0.20	0.30
b1	0.19	0.25
c	0.13	0.19
c1	0.12	0.14
D	4.86	5.06
E1	4.30	4.50
E	6.20	6.60
e	0.65BSC	
L	0.45	0.75
L1	1.00BSC	
θ	0	8°

6、Statements And Notes

6.1、The name and content of Hazardous substances or Elements in the product

Part name	Hazardous substances or Elements									
	Lead and lead compounds	Mercury and mercury compounds	Cadmium and cadmium compounds	Hexavalent chromium compounds	Polybrominated biphenyls	Polybrominated biphenyl ethers	Dibutyl phthalate	Butylbenzyl phthalate	Di-2-ethylhexyl phthalate	Diisobutyl phthalate
Lead frame	○	○	○	○	○	○	○	○	○	○
Plastic resin	○	○	○	○	○	○	○	○	○	○
Chip	○	○	○	○	○	○	○	○	○	○
The lead	○	○	○	○	○	○	○	○	○	○
Plastic sheet installed	○	○	○	○	○	○	○	○	○	○
explanation	○：Indicates that the content of hazardous substances or elements in the detection limit of the following the SJ/T11363-2006 standard. ×：Indicates that the content of hazardous substances or elements exceeding the SJ/T11363-2006 Standard limit requirements.									

6.2、Notion

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